

## isc N-Channel MOSFET Transistor

TK20G60W5

## • FEATURES

- Low drain-source on-resistance:  
 $R_{DS(ON)} \leq 155\text{m}\Omega$
- Easy to control Gate switching
- Enhancement mode:  
 $V_{TH} = 2.7 \text{ to } 3.7\text{V}$  ( $V_{DS} = 10\text{ V}$ ,  $I_D=1\text{mA}$ )
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## • DESCRIPTION

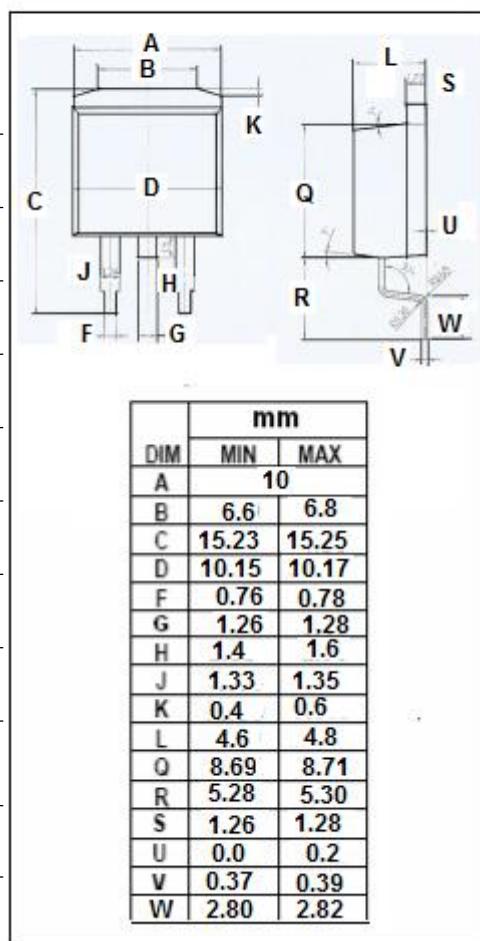
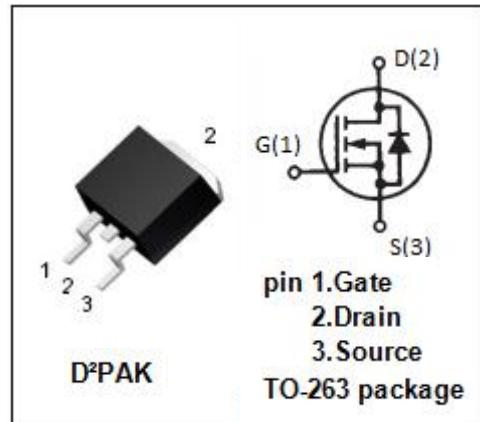
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER                                  | VALUE    | UNIT             |
|-----------|--|----------|------------------|
| $V_{DSS}$ | Drain-Source Voltage                       | 600      | V                |
| $V_{GS}$  | Gate-Source Voltage                        | $\pm 30$ | V                |
| $I_D$     | Drain Current-Continuous                   | 20       | A                |
| $I_{DM}$  | Drain Current-Single Pulsed                | 80       | A                |
| $P_D$     | Total Dissipation @ $T_c=25^\circ\text{C}$ | 165      | W                |
| $T_j$     | Max. Operating Junction Temperature        | 150      | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature                        | -55~150  | $^\circ\text{C}$ |

## • THERMAL CHARACTERISTICS

| SYMBOL         | PARAMETER                          | MAX   | UNIT                      |
|----------------|------------------------------------|-------|---------------------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance | 0.757 | $^\circ\text{C}/\text{W}$ |



**isc N-Channel MOSFET Transistor****TK20G60W5****ELECTRICAL CHARACTERISTICS**T<sub>c</sub>=25°C unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS                                   | MIN | TYP | MAX | UNIT |
|---------------------|--------------------------------|--|-----|-----|-----|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 10mA   | 600 |     |     | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> = 10V; I <sub>D</sub> =1mA   | 2.7 |     | 3.7 | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =10A   |     |     | 155 | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0V |     |     | ±1  | μA   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V |     |     | 10  | μA   |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>DR</sub> =20 A, V <sub>GS</sub> = 0 V |     |     | 1.7 | V    |

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